风光欣技术资料

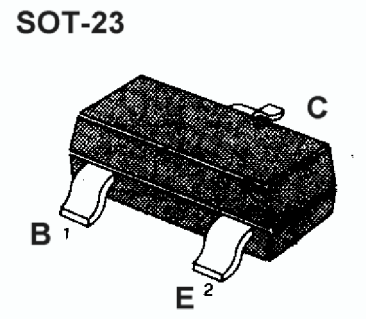
T9011

—NPN silicon —

APPLICATION: AM Converter, AM/FM IF Amplifier,
General Purpose Application.

MAXIMUM RATINGS （Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	30	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



1.Base 2 .Emitter 3 .Collector

ELECTRICAL CHARACTERISTICS （Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	28		198		V_{CE}= 5 V，Ic= 1 mA
Collector Cut-off Current	I_{CBO}			0.1	μA	V_{CB}=50 V，I_E=0
Emitter Cut-off Current	I_{EBO}			0.1	μA	V_{EB}= 5 V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	50			V	Ic=0.1 mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	30			V	Ic=1 mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	I_E= 0.1mA，Ic=0
Base-Emitter Voltage	V_{BE}		0.7	0.75	V	V_{CE}=5 V，Ic= 1mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.3	V	Ic=10 mA，I_B=1 mA
Gain bandwidth product	f_T	150	370		MHz	Ic= 1 mA，V_{CE}=5 V
Common Base Output Capacitance	Cob		2	3.5	PF	V_{CB}= 10V，I_E=0，f = 1 MHz
Noise Figure	N_F		2	4	dB	V_{CE}= 5 V,Ic= 1 mA,f=1MHz, Rg= 500Ω

h_{FE} **Classification And Marking**

Print Mark	11D	11E	11F	11G	11H	11I
Classification	D	E	F	G	H	I
h_{FE}	28～45	39～60	54～80	72～108	97～146	132～198